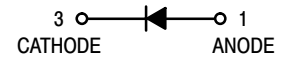
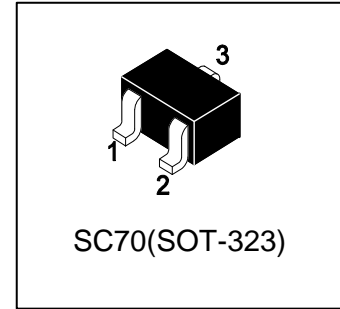


# LBAS16WT1G

## S-LBAS16WT1G

Silicon Switching Diode



### 1. FEATURES

- We declare that the material of product compliance with RoHS requirements and Halogen Free.
- S- prefix for automotive and other applications requiring unique site and control change requirements; AEC-Q101 qualified and PPAP capable.

### 2. DEVICE MARKING AND RESISTOR VALUES

Device	Marking	Shipping
LBAS16WT1G	A6	3000/Tape&Reel
LBAS16WT3G	A6	10000/Tape&Reel

### 3. MAXIMUM RATINGS(Ta = 25°C)

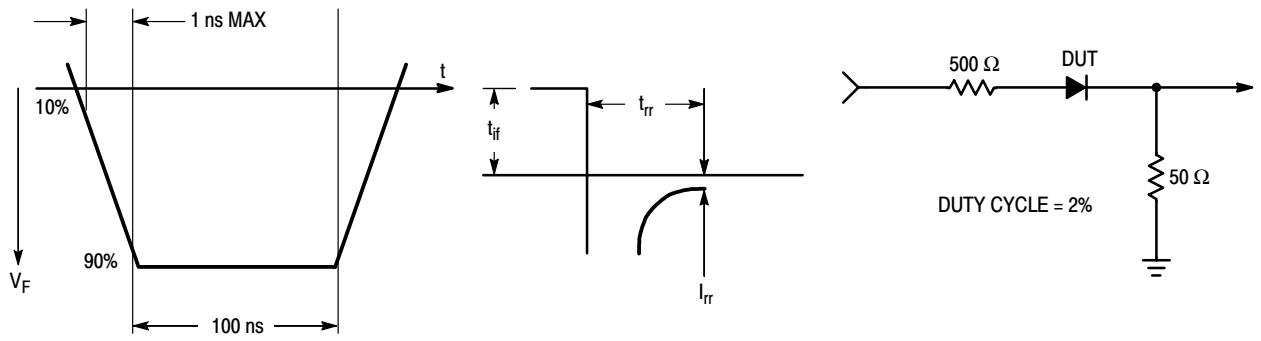
Parameter	Symbol	Limits	Unit
Continuous Reverse Voltage	VR	75	V
Peak Forward Current	IR	200	mA
Peak Forward Surge Current (Pulse Width = 10 μs)	IFSM	500	mA

### 4. THERMAL CHARACTERISTICS

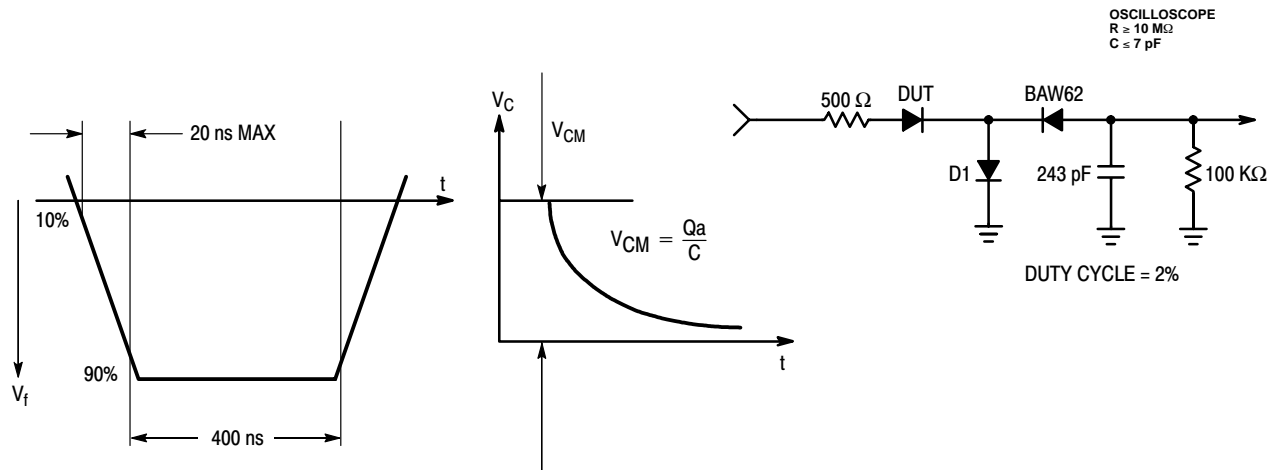
Parameter	Symbol	Limits	Unit
Total Power Dissipation, One Diode Loaded TA = 25°C	PD	200	mW
Derate above 25°C Mounted on a Ceramic Substrate(10 x 8 x 0.6 mm)		1.6	mW/°C
Thermal Resistance, Junction to Ambient One Diode Loaded Mounted on a Ceramic Substrate(10 x 8 x 0.6 mm)	RθJA	0.625	°C/mW
Junction and Storage Temperature	TJ , Tstg	-55~+150	°C

**5. ELECTRICAL CHARACTERISTICS (Ta= 25°C)**

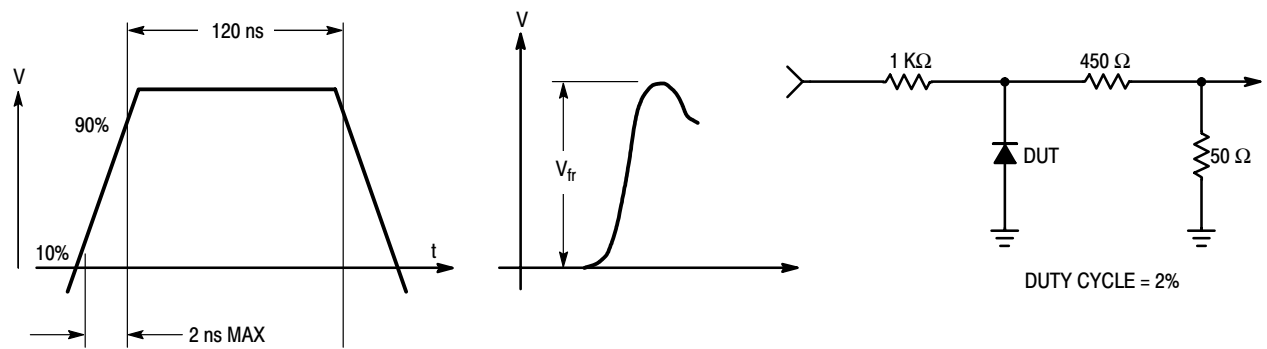
CHARACTERISTICS	Symbol	Min	Max	Unit
Forward voltage (IF =1mA)	VF	-	715	mV
(IF =10mA)		-	855	
(IF =50mA)		-	1000	
(IF =150mA)		-	1250	
Reverse Current (VR=75V)	IR	-	1	μA
(VR=75V, TJ = 150°C)		-	50	
(VR=25V, TJ = 150°C)		-	30	
Diode capacitance (f=1MHz,VR =0)	Cd	-	2	pF
Reverse Recovery Time (Figure 1) (IF = IR = 10mA, RL = 50Ω)	Trr	-	6	nS
Stored Charge (Figure 2) (IF = 10 mA to VR = 6.0V, RL = 500Ω)	QS	-	45	pC
Forward Recovery Voltage (Figure 3) (IF = 10 mA, tr = 20ns)	VFR	-	1.75	V



**Figure 1. Reverse Recovery Time Equivalent Test Circuit**

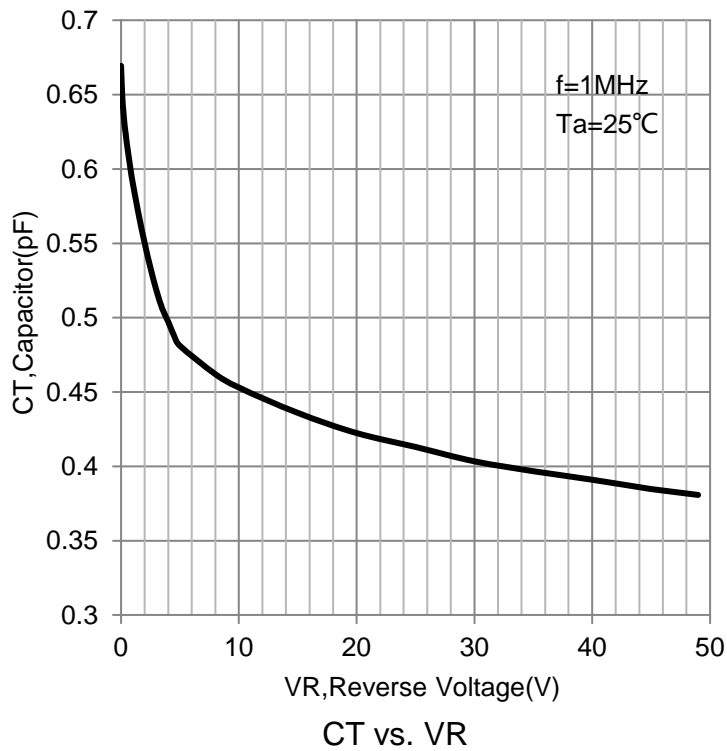
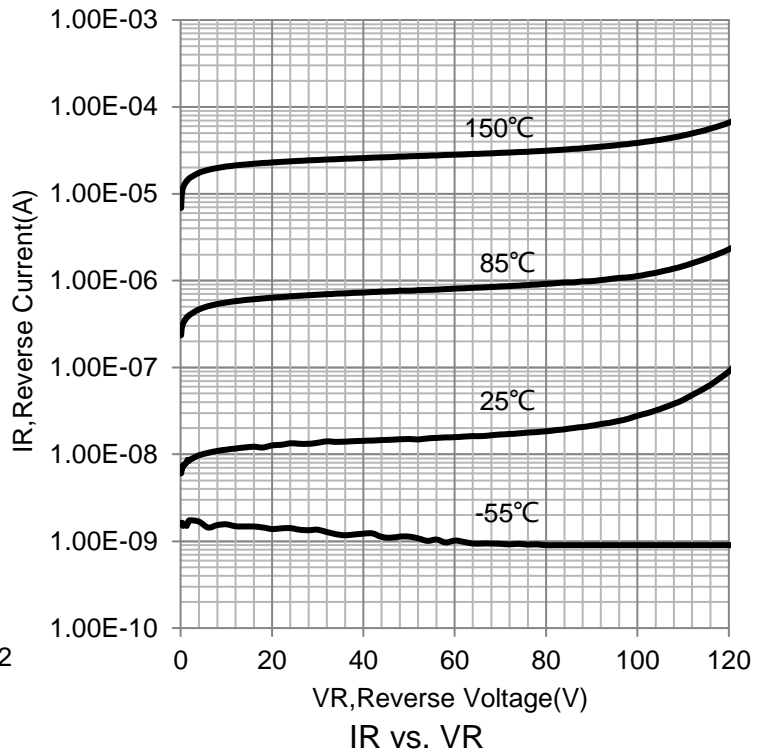
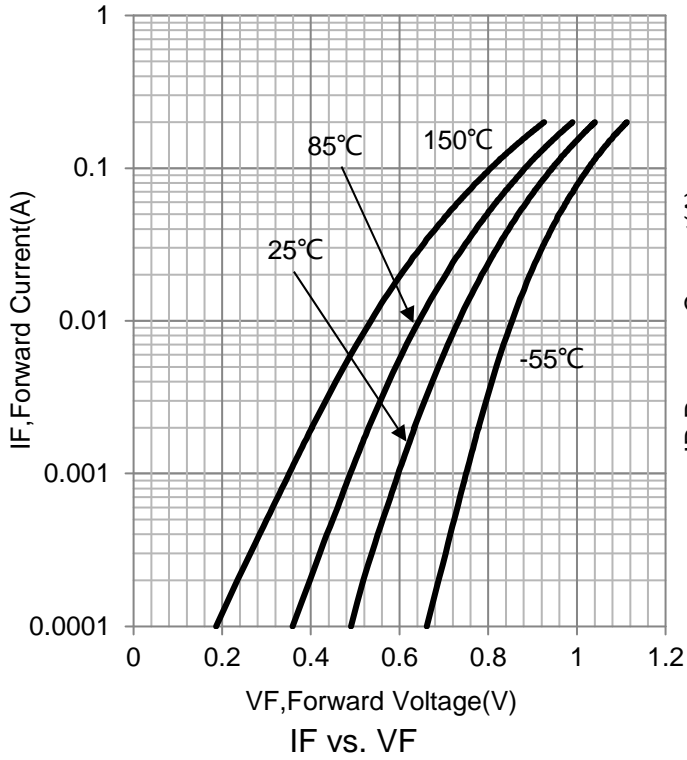


**Figure 2. Recovery Charge Equivalent Test Circuit**

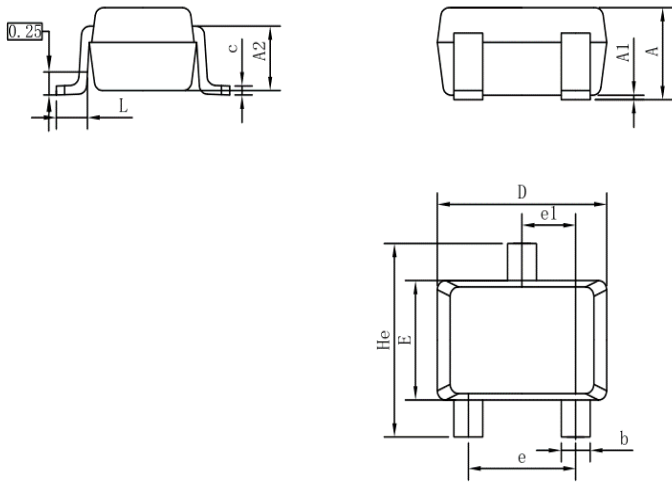


**Figure 3. Forward Recovery Voltage Equivalent Test Circuit**

**6.ELECTRICAL CHARACTERISTICS CURVES**

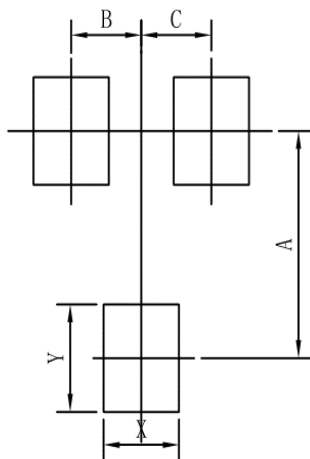


### 7. OUTLINE AND DIMENSIONS



SC70			
DIM	MIN	NOR	MAX
A	0.80	0.95	1.00
A1	0.00	0.05	0.10
A2	0.7 REF		
b	0.30	0.35	0.40
c	0.10	0.15	0.25
D	1.80	2.05	2.20
E	1.15	1.30	1.35
e	1.20	1.30	1.40
e1	0.65 BSC		
L	0.20	0.35	0.56
He	2.00	2.10	2.40
ALL Dimension in mm			

### 8. SOLDERING FOOTPRINT



SC70	
DIM	MIN
A	1.90
B	0.65
C	0.65
X	0.70
Y	0.90

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